

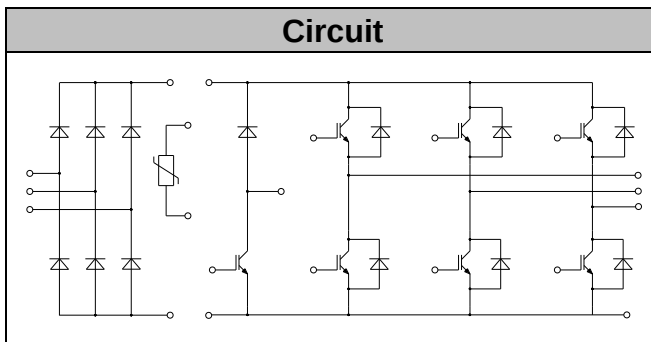


IGBT Modules

V_{CES}	1200V
I_C	75A

Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)



Features

- Low $V_{ce(sat)}$ with Trench technology
- Low $V_{ce(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175°C

● IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_c=100^{\circ}C, T_{vjmax}=175^{\circ}C$	75	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	150	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_c=25^{\circ}C, T_{vjmax}=175^{\circ}C$	476	W



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Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, $I_C=2.6mA$, $T_{vj}=25^{\circ}C$	5.8	6.5	7.2	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V$, $V_{GE}=0V$, $T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=75A$, $V_{GE}=15V$, $T_{vj}=25^{\circ}C$		1.85	2.15	V
		$I_C=75A$, $V_{GE}=15V$, $T_{vj}=125^{\circ}C$		2.05		
		$I_C=75A$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$		2.10		
Gate Charge	Q_G			0.78		uC
Input Capacitance	C_{ies}	$V_{CE}=25V$, $V_{GE}=0V$, $f=1MHz$, $T_{vj}=25^{\circ}C$		4.00		nF
Reverse Transfer Capacitance	C_{res}			0.30		nF
Internal Gate Resistance	R_{gint}			2.5		Ω
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V$, $V_{GE}=20V$, $T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=75A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=5.1\Omega$ $T_{vj}=25^{\circ}C$		100		ns
Rise Time	t_r			78		ns
Turn-off Delay Time	$t_{d(off)}$			380		ns
Fall Time	t_f			32		ns
Energy Dissipation During Turn-on Time	E_{on}			5.6		mJ
Energy Dissipation During Turn-off Time	E_{off}			3.6		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=75A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=5.1\Omega$ $T_{vj}=125^{\circ}C$		110		ns
Rise Time	t_r			85		ns
Turn-off Delay Time	$t_{d(off)}$			450		ns
Fall Time	t_f			36		ns
Energy Dissipation During Turn-on Time	E_{on}			8.8		mJ
Energy Dissipation During Turn-off Time	E_{off}			6.4		mJ
SC Data	I_{sc}	$T_p \leq 10\mu s$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$, $V_{cc}=900V$, $V_{CEM} \leq 1200V$		400		A



● Diode-inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		75	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	150	A

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=75\text{A}, T_{vj}=25^{\circ}\text{C}$		2.00	2.30	V
		$I_F=75\text{A}, T_{vj}=125^{\circ}\text{C}$		2.10		
		$I_F=75\text{A}, T_{vj}=150^{\circ}\text{C}$		2.15		
Recovered Charge	Q_{rr}	$I_F=75\text{A}$		4.2		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=900\text{A}/\mu\text{s}$		75		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		2.06		mJ
Recovered Charge	Q_{rr}	$I_F=75\text{A}$		9.6		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=900\text{A}/\mu\text{s}$		92		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=125^{\circ}\text{C}$		4.34		mJ



● IGBT-brake-chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_c=100^{\circ}C, T_{vjmax}=175^{\circ}C$	40	A
Repetitive Peak Collector Current	I_{CRM}	$tp=1ms$	80	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_c=25^{\circ}C, T_{vjmax}=175^{\circ}C$	300	W

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.2mA, T_{vj}=25^{\circ}C$	5.8	6.7	7.2	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=40A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.95	2.35	V
		$I_C=40A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.30		
		$I_C=40A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.40		
Gate Charge	Q_G			0.27		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		2.00		nF
Reverse Transfer Capacitance	C_{res}			0.07		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=40A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=12\Omega$ $T_{vj}=25^{\circ}C$		28		ns
Rise Time	t_r			16		ns
Turn-off Delay Time	$t_{d(off)}$			26		ns
Fall Time	t_f			125		ns
Energy Dissipation During Turn-on Time	E_{on}			2.40		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.25		mJ



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Turn-on Delay Time	$t_{d(on)}$	$I_C = 40\text{ A}$ $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 12\Omega$ $T_{vj} = 125^\circ\text{C}$		28		ns
Rise Time	t_r			18		ns
Turn-off Delay Time	$t_{d(off)}$			310		ns
Fall Time	t_f			190		ns
Energy Dissipation During Turn-on Time	E_{on}			3.60		mJ
Energy Dissipation During Turn-off Time	E_{off}			3.20		mJ
SC Data	I_{sc}	$T_p \leq 10\mu\text{s}, V_{GE} = 15\text{ V}, T_{vj} = 150^\circ\text{C},$ $V_{cc} = 900\text{ V}, V_{CEM} \leq 1200\text{ V}$		130		A

● Diode-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_j = 25^\circ\text{C}$	1200	V
Continuous DC Forward Current	I_F		40	A
Repetitive Peak Forward Current	I_{FRM}	$t_p = 1\text{ ms}$	80	A
I^2t -value	I^2t	$V_R = 0, t_p = 10\text{ ms}, T_j = 125^\circ\text{C}$	240	A^2s
		$V_R = 0, t_p = 10\text{ ms}, T_j = 150^\circ\text{C}$	220	

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F = 40\text{ A}, T_{vj} = 25^\circ\text{C}$		1.75	2.25	V
		$I_F = 40\text{ A}, T_{vj} = 125^\circ\text{C}$		1.75		
		$I_F = 40\text{ A}, T_{vj} = 150^\circ\text{C}$		1.75		
Recovered Charge	Q_{rr}	$I_F = 40\text{ A}$		4.15		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 600\text{ V}$ $-di_F/dt = 1600\text{ A}/\mu\text{s}$		42		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 25^\circ\text{C}$		1.30		mJ



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Recovered Charge	Q_{rr}	$I_F = 40\text{ A}$		8.00		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 600\text{ V}$ $-di_F/dt = 1600\text{ A}/\mu\text{s}$		46		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 125^\circ\text{C}$		2.38		mJ

● Diode-Rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_j = 25^\circ\text{C}$	1600	V
Average On-state Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_c = 80^\circ\text{C}$	80	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_c = 80^\circ\text{C}$	120	A
Surge Forward Current	I_{FSM}	$V_R = 0, t_p = 10\text{ ms}, T_j = 45^\circ\text{C}$	1100	A
I^2t -value	I^2t	$V_R = 0, t_p = 10\text{ ms}, T_j = 45^\circ\text{C}$	6050	A^2s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F = 50\text{ A}, T_j = 150^\circ\text{C}$		0.98		V
Reverse Current	I_R	$T_j = 125^\circ\text{C}, V_R = 1600\text{ V}$			2.0	mA

● NTC-Thermistor

Characteristic values

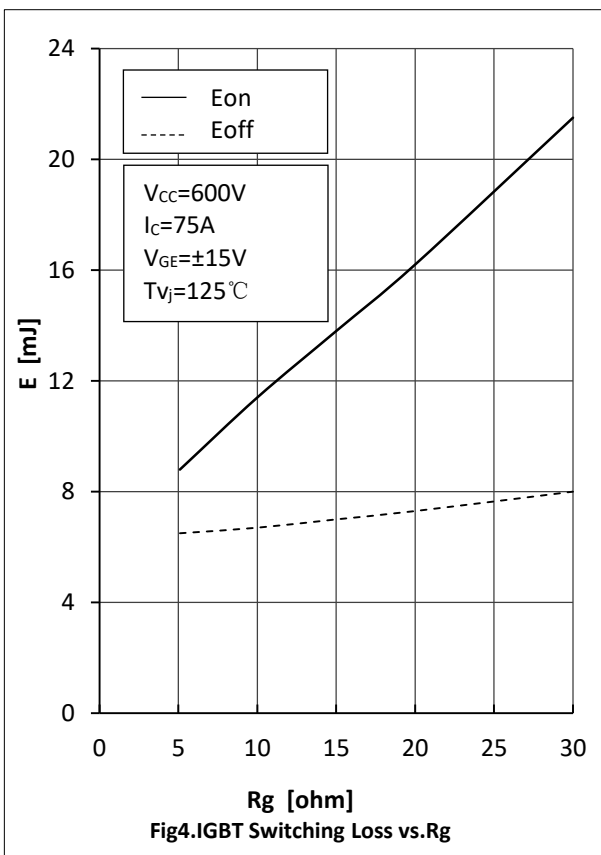
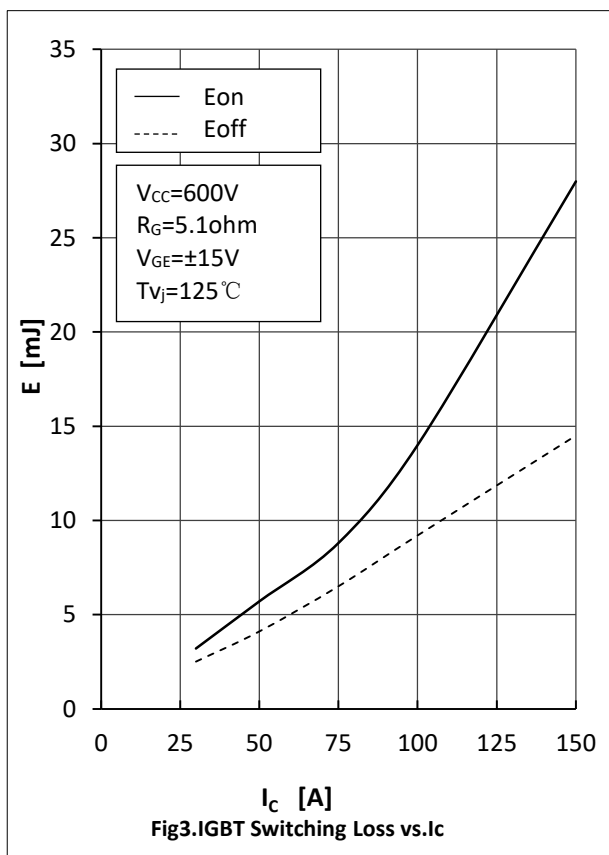
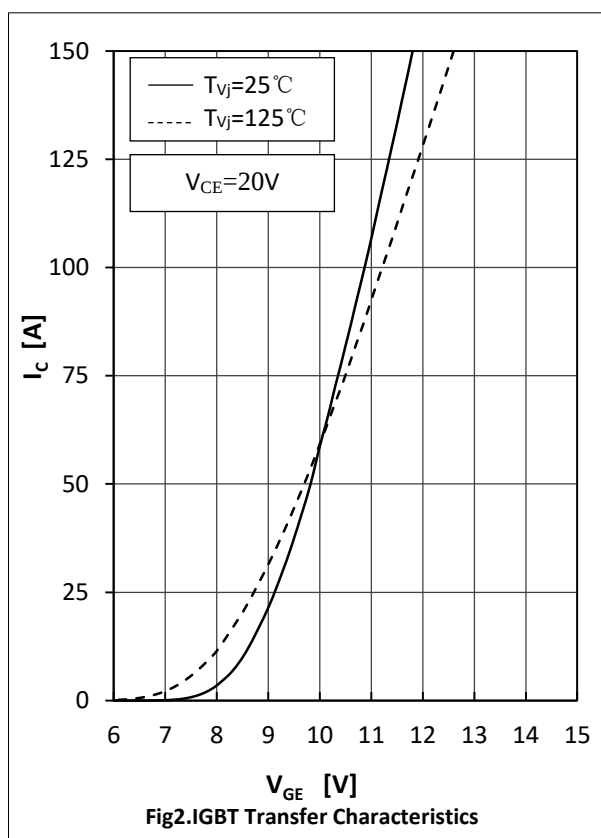
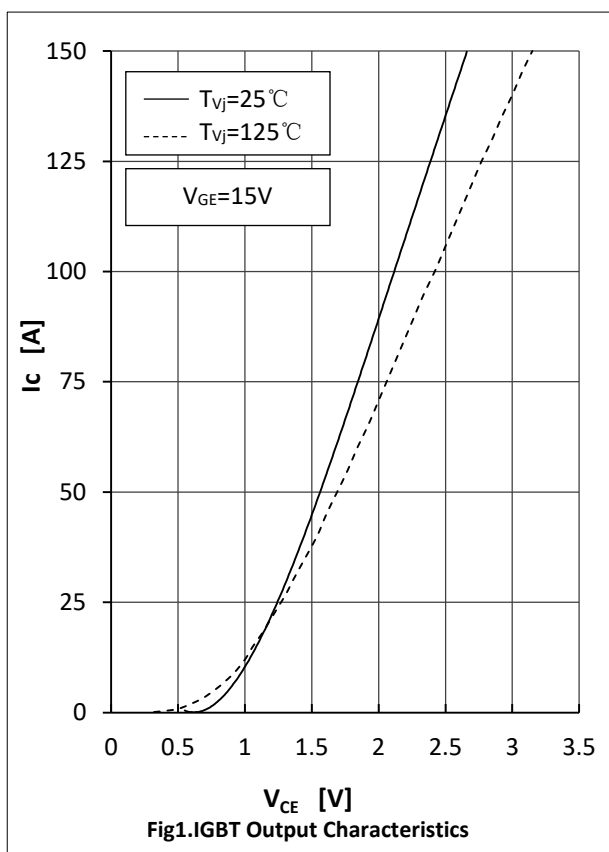
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		$\text{k}\Omega$
Deviation of R_{100}	$\Delta R/R$	$T_C = 100, R_{100} = 493.3\Omega$	-5		5	%
Power Dissipation	P_{25}			20.0		mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298.15\text{K}))]$		3375		K

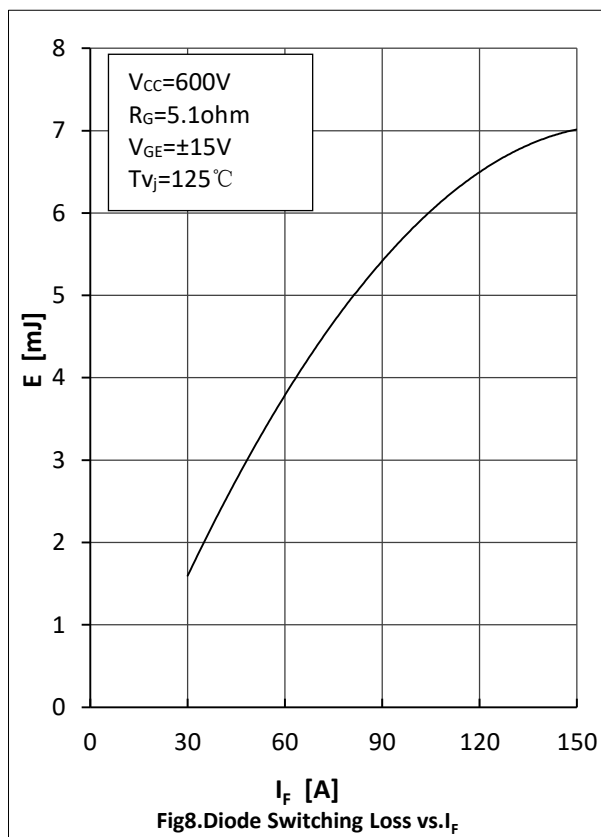
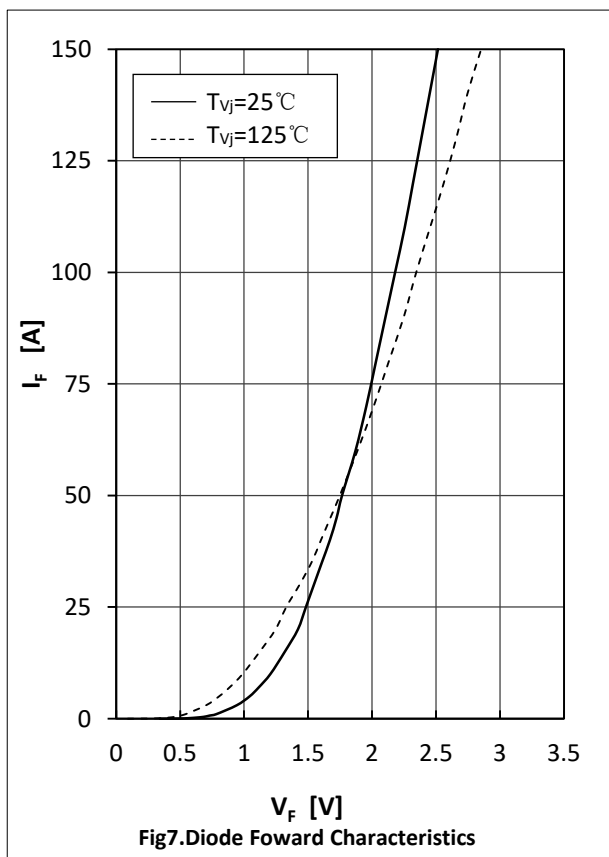
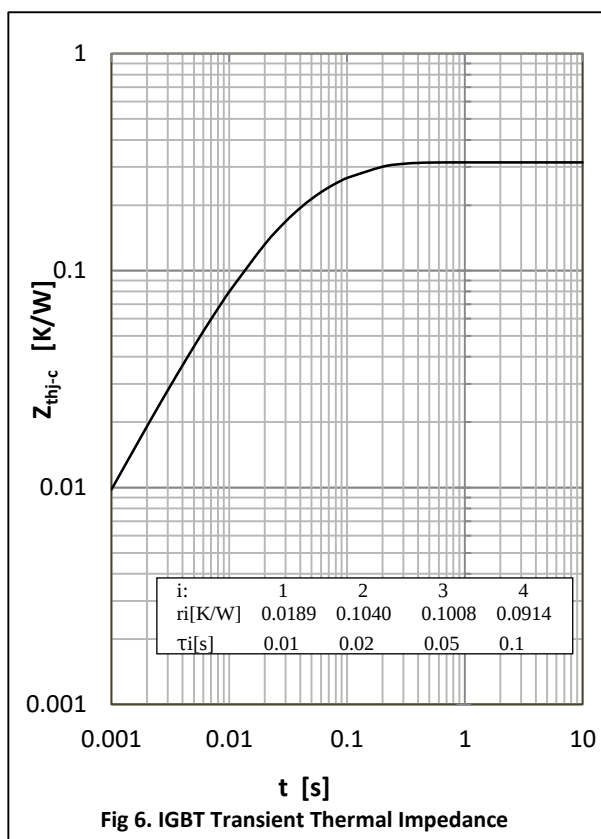
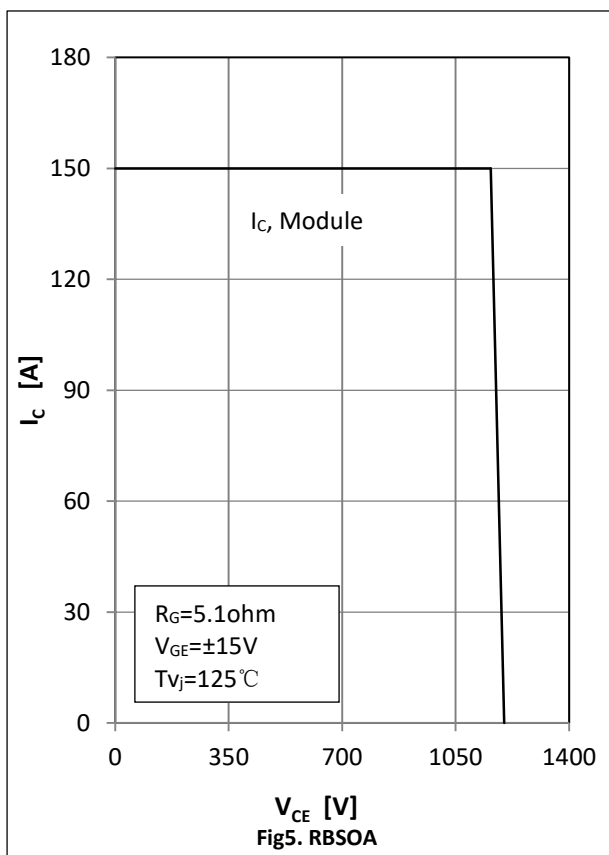


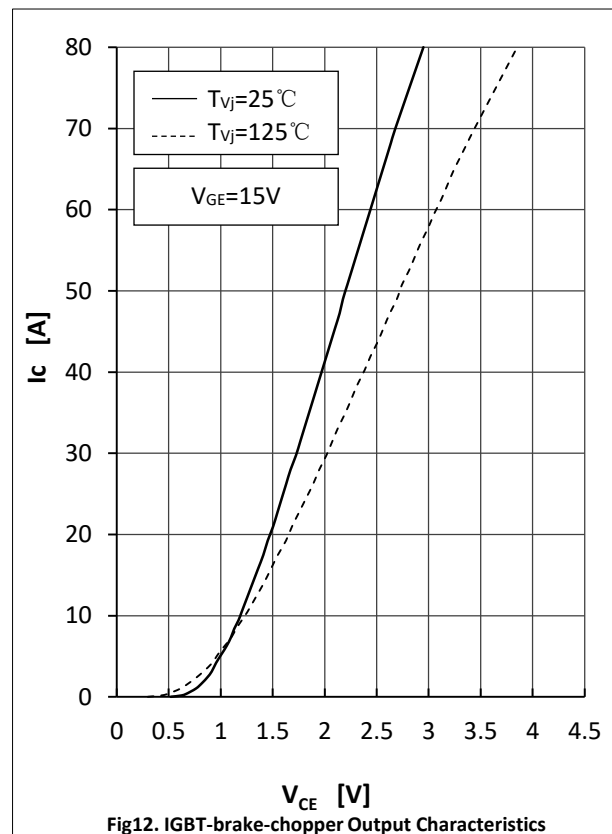
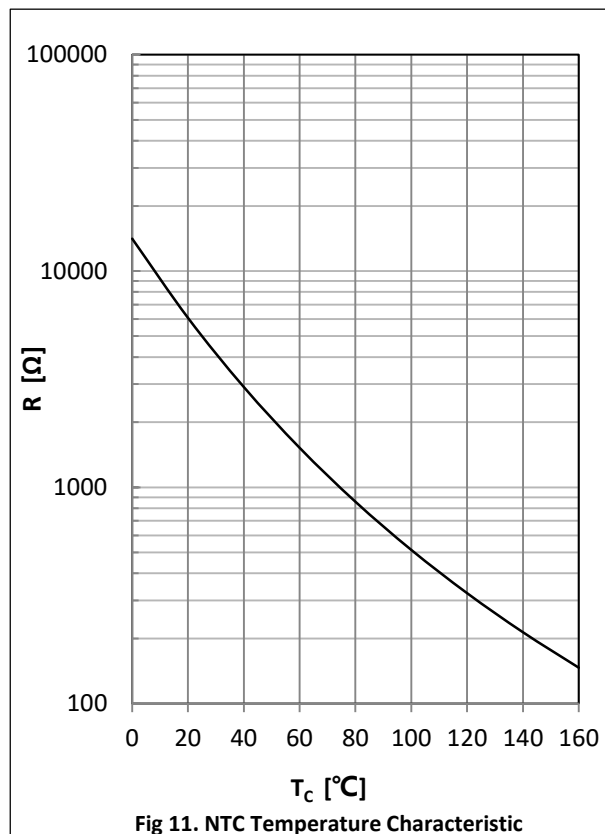
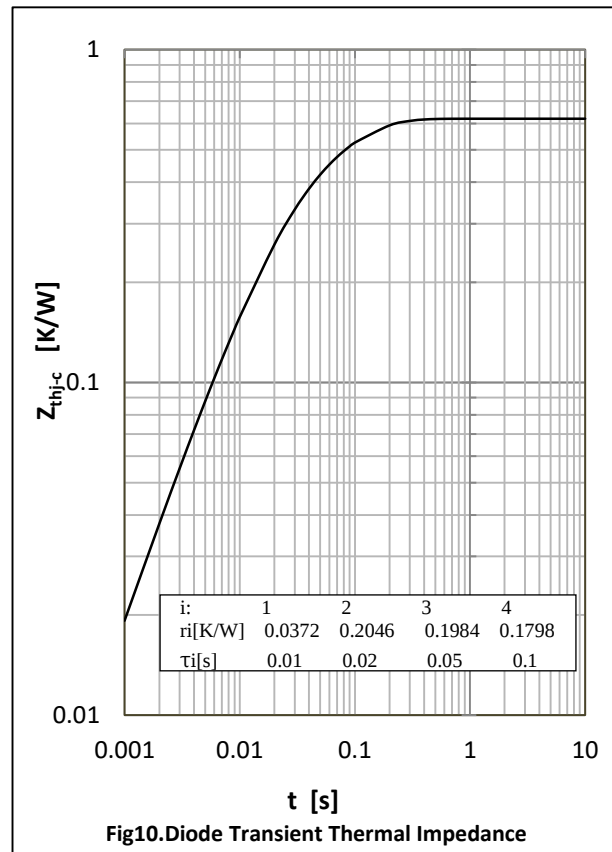
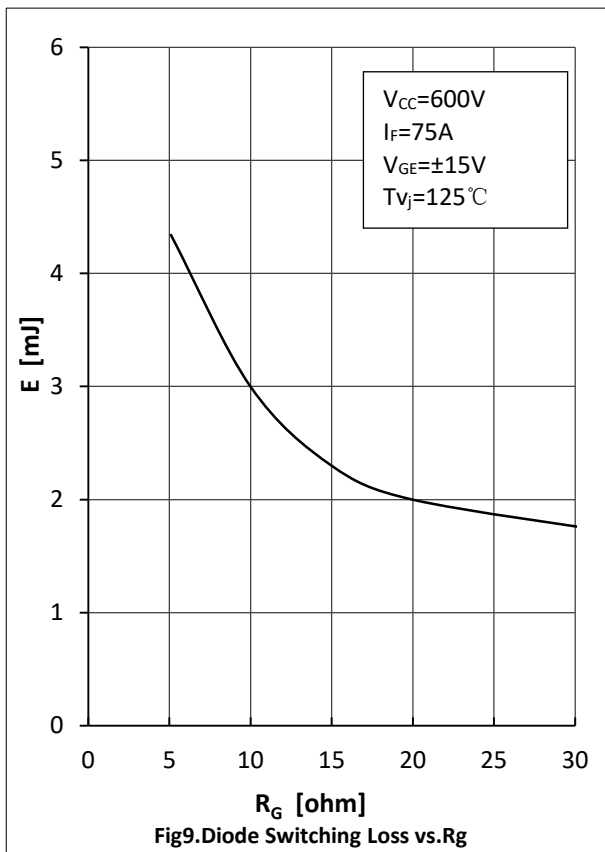
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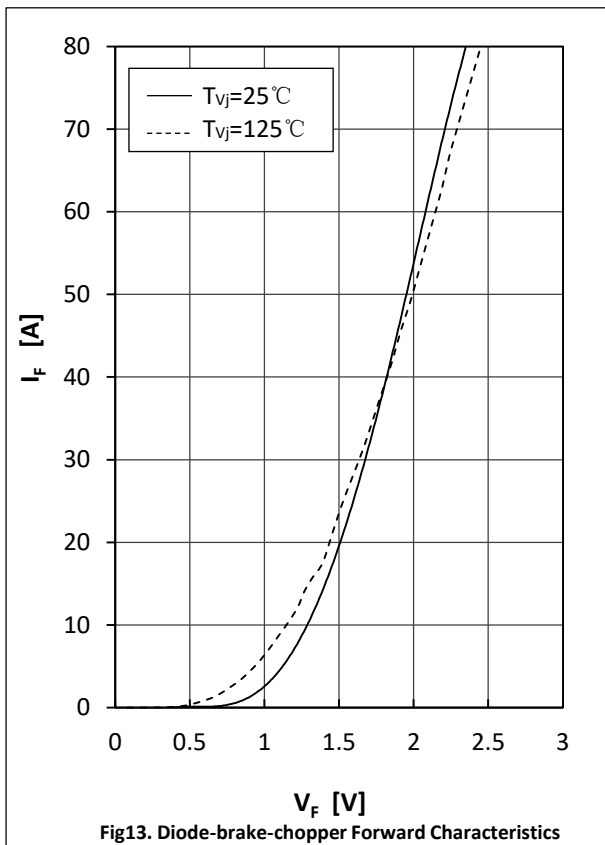
● Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{j\text{max}}$	Inverter, brake			175	$^{\circ}\text{C}$
		rectifier			150	
Operating Junction Temperature	$T_{vj\text{op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Stray Inductance	L_{CE}			60		nH
Module Lead Resistance ,Terminal to Chip	$R_{\text{cc}'+\text{EE}'}$	$T_C=25^{\circ}\text{C}$, per switch		4.0		$\text{m}\Omega$
	$R_{\text{AA}'+\text{CC}'}$			2.0		
Thermal Resistance Junction-to Case	$R_{\theta\text{jc}}$	per IGBT-inverter			0.315	K/W
		per Diode-inverter			0.620	
		per IGBT-brake-copper			0.500	
		per Diode-chopper			1.266	
		per Diode-rectifier			0.548	
Thermal Resistance Case-to Sink	$R_{\theta\text{CS}}$	per IGBT-inverter		0.118		K/W
		per Diode-inverter		0.205		
		per IGBT-brake-copper		0.180		
		per Diode-chopper		0.452		
		per Diode-rectifier		0.236		
		per Module		0.009		
Module-to-Sink Torque	M_s		3.0		6.0	N·m
Weight of Module	G			300		g

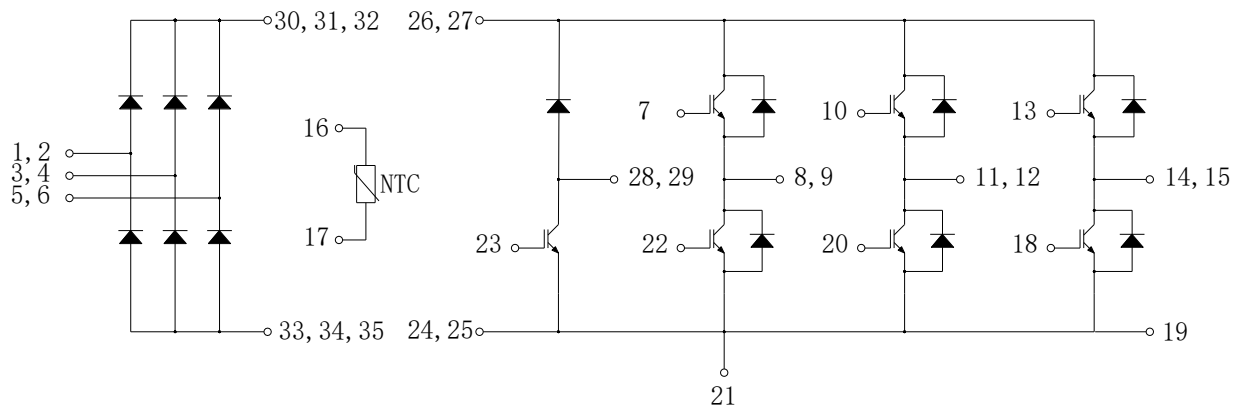








● Circuit Diagram



● Package Dimensions

